

Double channel high-side driver with analog current sense for 24 V automotive applications

Datasheet – production data

Features

| | | |
|-----------------------------------|-----------|---------------|
| Max transient supply voltage | V_{CC} | 58 V |
| Operating voltage range | V_{CC} | 8 to 36 V |
| Typ on-state resistance (per ch.) | R_{ON} | 35 m Ω |
| Current limitation (typ) | I_{LIM} | 42 A |
| Off-state supply current | I_S | 2 μ A |

- General
 - Very low standby current
 - 3.0 V CMOS compatible input
 - Optimized electromagnetic emission
 - Very low electromagnetic susceptibility
 - In compliance with the 2002/95/EC European directive
 - Fault reset standby pin (FR_Stby)
 - Optimized for LED application
- Diagnostic functions
 - Proportional load current sense
 - High current sense precision for wide range currents
 - Off-state open load detection
 - Output short to V_{CC} detection
 - Overload and short to ground latch off
 - Thermal shutdown latch-off
 - Very low current sense leakage
- Protections
 - Undervoltage shutdown
 - Overvoltage clamp
 - Load current limitation
 - Self limiting of fast thermal transients
 - Protection against loss of ground and loss of V_{CC}
 - Thermal shutdown
 - Electrostatic discharge protection



Application

All types of resistive, inductive and capacitive loads

Description

The VND5T035LAK-E is a monolithic device made using STMicroelectronics® VIPower® technology, intended for driving resistive or inductive loads with one side connected to ground. Active V_{CC} pin voltage clamp protects the device against low energy spikes.

The device integrates an analog current sense which delivers a current proportional to the load current.

Fault conditions such as overload, overtemperature or short to V_{CC} are reported via the current sense pin.

Output current limitation protects the device in overload conditions. The device latches off in case of overload or thermal shutdown.

The device is reset by a low level pass on the fault reset standby pin.

A permanent low level on the inputs and on the fault reset standby pins disables all outputs and sets the device in standby mode.

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1 Block diagram and pin description

Figure 1. Block diagram

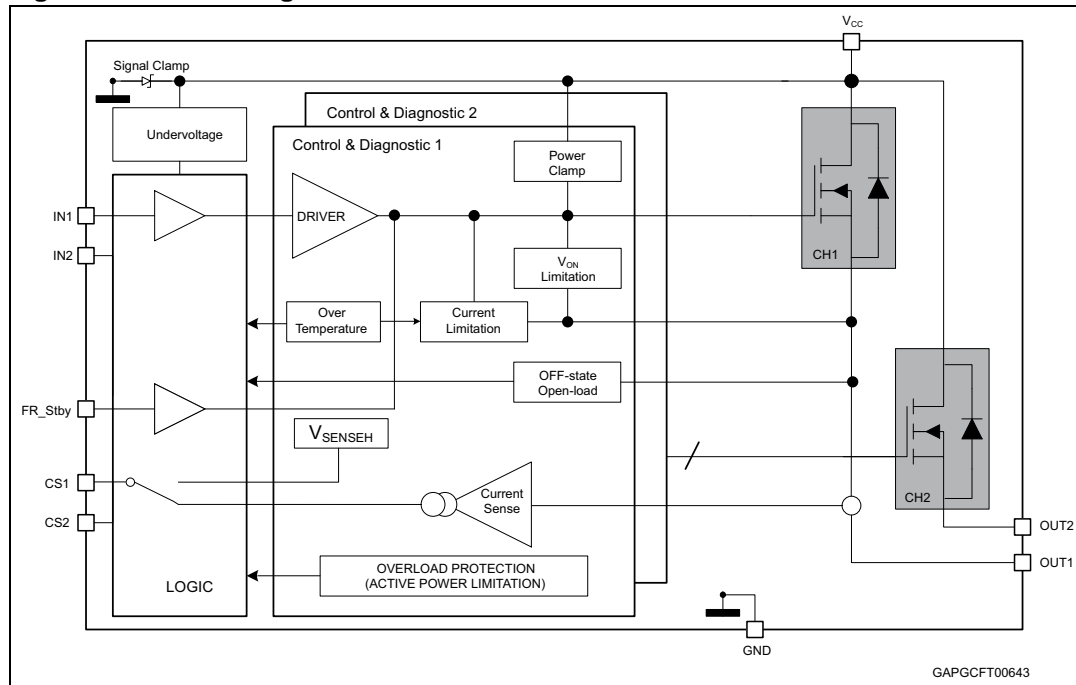


Table 1. Pin function

| Name | Function |
|------------------|--|
| V _{CC} | Battery connection |
| OUT _n | Power output |
| GND | Ground connection |
| IN _n | Voltage controlled input pin with hysteresis, CMOS compatible. It controls output switch state |
| CS _n | Analog current sense pin; it delivers a current proportional to the load current |
| FR_Stby | In case of latch-off for overtemperature/overcurrent condition, a low pulse on the FR_Stby pin is needed to reset the channel. The device enters in standby mode if all inputs and the FR_Stby pin are low. |

Figure 2. Configuration diagram PowerSSO-24 (top view)

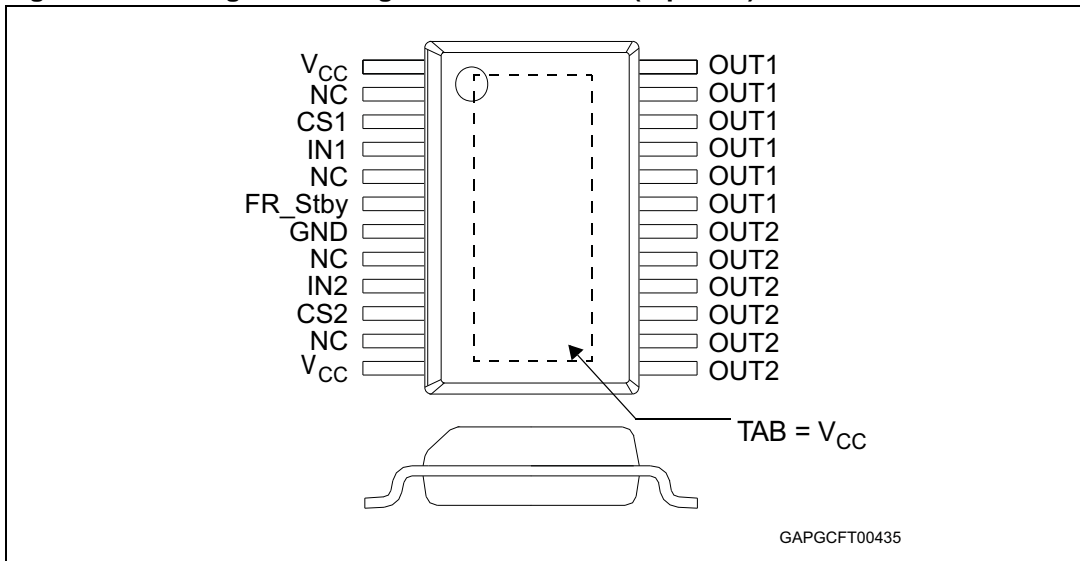


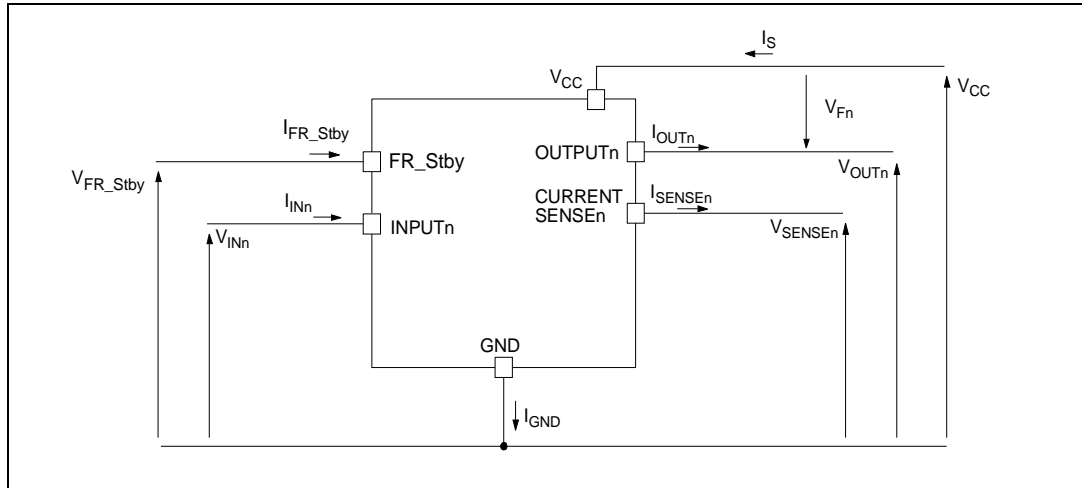
Table 2. Suggested connections for unused and not connected pins

| Connection / pin | CurrentSense | N.C. | Output | Input | FR_Stby |
|------------------|------------------------|------------------|-------------|------------------------|---------------|
| Floating | Not allowed | X ⁽¹⁾ | X | X | X |
| To ground | Through 10 KΩ resistor | X | Not allowed | Through 10 KΩ resistor | Through 10 KΩ |

1. X: do not care.

2 Electrical specifications

Figure 3. Current and voltage conventions



Note: $V_{Fn} = V_{OUTn} - V_{CC}$ during reverse battery condition.

2.1 Absolute maximum ratings

Stressing the device above the ratings listed in [Table 3](#) may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied.

Table 3. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|--|----------------------------|------|
| V_{CC} | DC supply voltage | 58 | V |
| $-V_{CC}$ | Reverse DC supply voltage | 0.3 | V |
| $-I_{GND}$ | DC reverse ground pin current | 200 | mA |
| I_{OUT} | DC output current | Internally limited | A |
| $-I_{OUT}$ | Reverse DC output current | 40 | A |
| I_{IN} | DC input current | -1 to 10 | mA |
| I_{FR_Stby} | Fault reset standby DC input current | -1 to 1.5 | mA |
| $-I_{CSENSE}$ | DC reverse CS pin current | 200 | mA |
| V_{CSENSE} | Current sense maximum voltage | $V_{CC} - 58$ to $+V_{CC}$ | V |
| E_{MAX} | Maximum switching energy ($L = 2.3$ mH; $V_{BAT} = 32$ V; $T_{jstart} = 150$ °C; $I_{OUT} = I_{limL}$ (typ)) | 250 | mJ |

Table 3. Absolute maximum ratings (continued)

| Symbol | Parameter | Value | Unit |
|------------|--|------------|------------------|
| L_{smax} | Maximum strain inductance in short circuit condition $R_L = 300\text{ m}\Omega$, $V_{BAT} = 32\text{ V}$, $T_{jstart} = 150\text{ }^\circ\text{C}$, $I_{OUT} = I_{LMHmax}$ | 40 | μH |
| V_{ESD} | Electrostatic discharge (Human Body Model: $R = 1.5\text{ K}\Omega$; $C = 100\text{ pF}$) | | |
| | – INPUT | 4000 | V |
| | – CURRENT SENSE | 2000 | V |
| | – FR_Stby | 4000 | V |
| | – OUTPUT | 5000 | V |
| | – V_{CC} | 5000 | V |
| V_{ESD} | Charge device model (CDM-AEC-Q100-011) | 750 | V |
| T_j | Junction operating temperature | -40 to 150 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | -55 to 150 | $^\circ\text{C}$ |

2.2 Thermal data

Table 4. Thermal data

| Symbol | Parameter | Value | Unit |
|----------------|--|-------------------------------|--------------------|
| $R_{thj-case}$ | Thermal resistance junction-case (max) (with one channel ON) | 2 | $^\circ\text{C/W}$ |
| $R_{thj-amb}$ | Thermal resistance junction-ambient (max) | See Figure 27 | $^\circ\text{C/W}$ |

2.3 Electrical characteristics

$8\text{ V} < V_{CC} < 36\text{ V}$; $-40^{\circ}\text{C} < T_j < 150^{\circ}\text{C}$, unless otherwise specified.

Table 5. Power section

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|------------------------------------|---|------|------------------|------------------|---------------|
| V_{CC} | Operating supply voltage | | 8 | 24 | 36 | V |
| V_{USD} | Undervoltage shutdown | | | 3.5 | 5 | V |
| $V_{USDhyst}$ | Undervoltage shutdown hysteresis | | | 0.5 | | V |
| R_{ON} | On-state resistance ⁽¹⁾ | $I_{OUT} = 3\text{ A}$; $T_j = 25^{\circ}\text{C}$ | | 35 | | m Ω |
| | | $I_{OUT} = 3\text{ A}$; $T_j = 150^{\circ}\text{C}$ | | | 70 | |
| V_{clamp} | Clamp voltage | $I_S = 20\text{ mA}$ | 58 | 64 | 70 | V |
| I_S | Supply current | Off-state; $V_{CC} = 24\text{ V}$; $T_j = 25^{\circ}\text{C}$; $V_{IN} = V_{OUT} = V_{SENSE} = 0\text{ V}$ | | 2 ⁽²⁾ | 5 ⁽²⁾ | μA |
| | | On-state; $V_{CC} = 24\text{ V}$; $V_{IN} = 5\text{ V}$; $I_{OUT} = 0\text{ A}$ | | 4.2 | 6 | mA |
| $I_{L(off)}$ | Off-state output current | $V_{IN} = V_{OUT} = 0\text{ V}$; $V_{CC} = 24\text{ V}$; $T_j = 25^{\circ}\text{C}$ | 0 | 0.01 | 3 | μA |
| | | $V_{IN} = V_{OUT} = 0\text{ V}$; $V_{CC} = 24\text{ V}$; $T_j = 125^{\circ}\text{C}$ | 0 | | 5 | |
| V_F | Output - V_{CC} diode voltage | $-I_{OUT} = 3\text{ A}$; $T_j = 150^{\circ}\text{C}$ | | | 0.7 | V |

1. For each channel

2. PowerMOS leakage included

Table 6. Switching ($V_{CC} = 24\text{ V}$; $T_j = 25^{\circ}\text{C}$)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------------|---|-------------------|------|------|------|------------------|
| $t_{d(on)}$ | Turn-on delay time | $R_L = 8\ \Omega$ | | 46 | | μs |
| $t_{d(off)}$ | Turn-off delay time | $R_L = 8\ \Omega$ | | 54 | | μs |
| $dV_{OUT}/dt_{(on)}$ | Turn-on voltage slope | $R_L = 8\ \Omega$ | | 0.55 | | V/ μs |
| $dV_{OUT}/dt_{(off)}$ | Turn-off voltage slope | $R_L = 8\ \Omega$ | | 0.46 | | V/ μs |
| W_{ON} | Switching energy losses during t_{won} | $R_L = 8\ \Omega$ | | 1 | | mJ |
| W_{OFF} | Switching energy losses during t_{woff} | $R_L = 8\ \Omega$ | | 0.65 | | mJ |

Table 7. Logic inputs

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|----------------------|--|---------------------------------------|------|------|------|---------------|
| V_{IL} | Input low level voltage | | | | 0.9 | V |
| I_{IL} | Low level input current | $V_{IN} = 0.9\text{ V}$ | 1 | | | μA |
| V_{IH} | Input high level voltage | | 2.1 | | | V |
| I_{IH} | High level input current | $V_{IN} = 2.1\text{ V}$ | | | 10 | μA |
| $V_{I(hyst)}$ | Input hysteresis voltage | | 0.25 | | | V |
| V_{ICL} | Input clamp voltage | $I_{IN} = 1\text{ mA}$ | 5.5 | | 7 | V |
| | | $I_{IN} = -1\text{ mA}$ | | -0.7 | | V |
| $V_{FR_Stby_L}$ | Fault_reset_standby low level voltage | | | | 0.9 | V |
| $I_{FR_Stby_L}$ | Low level fault_reset_standby current | $V_{FR_Stby} = 0.9\text{ V}$ | 1 | | | μA |
| $V_{FR_Stby_H}$ | Fault_reset_standby high level voltage | | 2.1 | | | V |
| $I_{FR_Stby_H}$ | High level fault_reset_standby current | $V_{FR_Stby} = 2.1\text{ V}$ | | | 10 | μA |
| $V_{FR_Stby(hyst)}$ | Fault_reset_standby hysteresis voltage | | 0.25 | | | V |
| $V_{FR_Stby_CL}$ | Fault_reset_standby clamp voltage | $I_{FR_Stby} = 15\text{ mA (10 ms)}$ | 11 | | 15 | V |
| | | $I_{FR_Stby} = -1\text{ mA}$ | | -0.7 | | V |
| t_{reset} | Overload latch-off reset time | See Figure 4 | 2 | | 24 | μs |
| t_{stby} | Standby delay | See Figure 5 | 120 | | 1200 | μs |

Figure 4. Treset definition

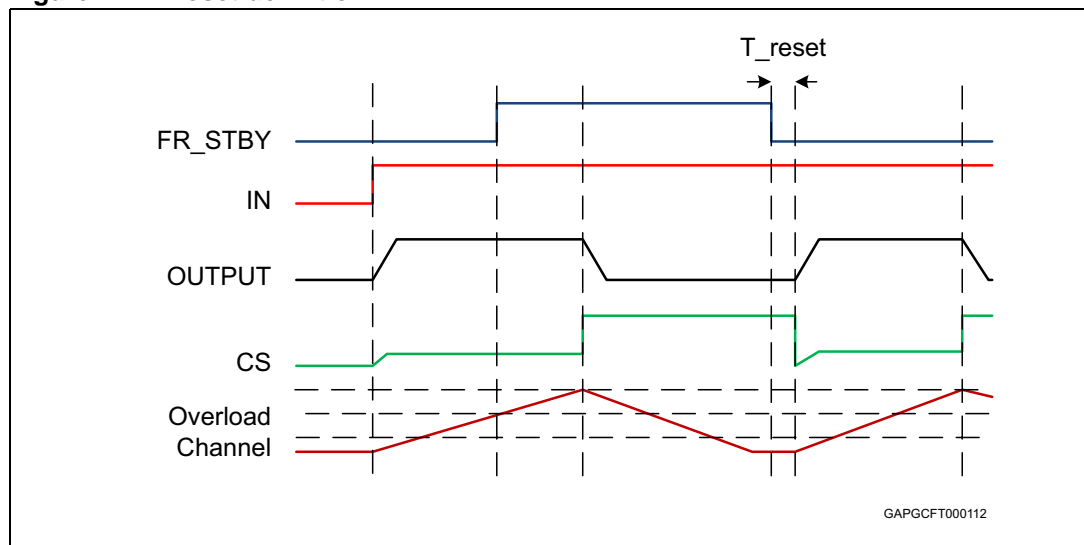


Figure 5. Tstby definition

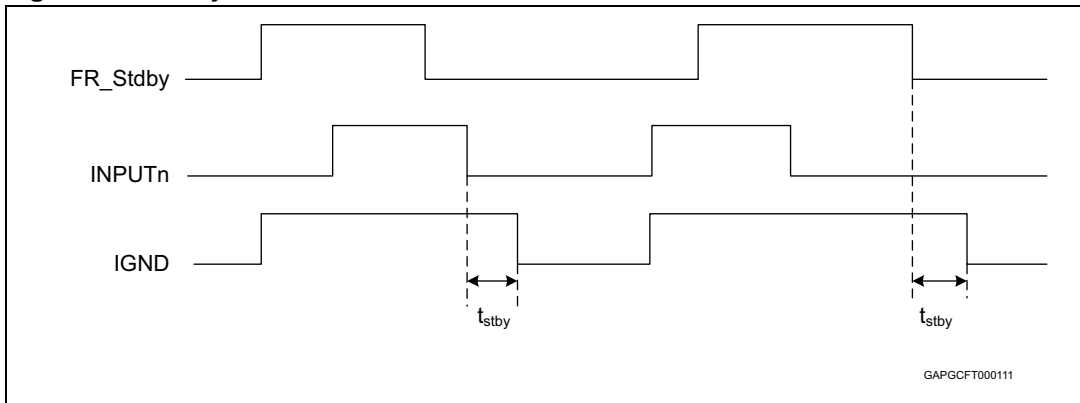


Table 8. Protections and diagnostics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------------|--|--|----------------------|----------------------|----------------------|------|
| I _{limH} | DC short circuit current | V _{CC} = 24V | 30 | 42 | 55 | A |
| | | 5 V < V _{CC} < 36 V | | | 55 | A |
| I _{limL} | Short circuit current during thermal cycling | V _{CC} = 24 V; T _R < T _j < T _{TSD} | | 10.5 | | A |
| T _{TSD} | Shutdown temperature | | 150 | 175 | 200 | °C |
| T _R | Reset temperature | | T _{RS} + 1 | T _{RS} + 5 | | °C |
| T _{RS} | Thermal reset of status | | 135 | | | °C |
| T _{HYST} | Thermal hysteresis (T _{TSD} -T _R) | | | 7 | | °C |
| V _{DEMAG} | Turn-off output voltage clamp | I _{OUT} = 3 A; V _{IN} = 0; L = 6 mH | V _{CC} - 58 | V _{CC} - 64 | V _{CC} - 70 | V |
| V _{ON} | Output voltage drop limitation | I _{OUT} = 150 mA; T _j = -40°C to 150°C | | 25 | | mV |

Table 9. Current sense ($8\text{ V} < V_{CC} < 36\text{ V}$)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-------------------------------|---|---|------|------|------|---------------|
| K_{OL} | I_{OUT}/I_{SENSE} | $I_{OUT} = 12\text{ mA}; V_{SENSE} = 0.5\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | 820 | | | |
| | | $I_{OUT} = 12\text{ mA}; V_{SENSE} = 0.5\text{ V}; T_j = 25^\circ\text{C to } 150^\circ\text{C}$ | 1357 | | | |
| K_{LED} | I_{OUT}/I_{SENSE} | $I_{OUT} = 60\text{ mA}; V_{SENSE} = 0.5\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | 1690 | 4160 | 7210 | |
| | | $I_{OUT} = 60\text{ mA}; V_{SENSE} = 0.5\text{ V}; T_j = 25^\circ\text{C to } 150^\circ\text{C}$ | 2040 | | 6460 | |
| $dK_{LED}/K_{LEDTOT}^{(1)}$ | Current sense ratio drift | $I_{OUT} = 12\text{ mA to } 60\text{ mA}; I_{CAL} = 35\text{ mA}; V_{SENSE} = 0.5\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | -40 | | 40 | % |
| K_0 | I_{OUT}/I_{SENSE} | $I_{OUT} = 100\text{ mA}; V_{SENSE} = 0.5\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | 2215 | 4030 | 6305 | |
| $dK_0/K_0^{(1)}$ | Current sense ratio drift | $I_{OUT} = 100\text{ mA}; V_{SENSE} = 0.5\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | -20 | | 20 | % |
| K_1 | I_{OUT}/I_{SENSE} | $I_{OUT} = 0.8\text{ A}; V_{SENSE} = 1\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | 2210 | 3400 | 4590 | |
| $dK_1/K_1^{(1)}$ | Current sense ratio drift | $I_{OUT} = 0.8\text{ A}; V_{SENSE} = 1\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | -18 | | 18 | % |
| K_2 | I_{OUT}/I_{SENSE} | $I_{OUT} = 1.6\text{ A}; V_{SENSE} = 2\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | 2541 | 3385 | 4059 | |
| $dK_2/K_2^{(1)}$ | Current sense ratio drift | $I_{OUT} = 1.6\text{ A}; V_{SENSE} = 2\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | -14 | | 14 | % |
| K_3 | I_{OUT}/I_{SENSE} | $I_{OUT} = 2.4\text{ A}; V_{SENSE} = 4\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | 2706 | 3360 | 3894 | |
| $dK_3/K_3^{(1)}$ | Current sense ratio drift | $I_{OUT} = 2.4\text{ A}; V_{SENSE} = 4\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | -10 | | 10 | % |
| K_4 | I_{OUT}/I_{SENSE} | $I_{OUT} = 12\text{ A}; V_{SENSE} = 4\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | 3055 | 3313 | 3445 | |
| $dK_4/K_4^{(1)}$ | Current sense ratio drift | $I_{OUT} = 12\text{ A}; V_{SENSE} = 4\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | -4 | | 4 | % |
| $dK_{BULB}/K_{BULBTOT}^{(1)}$ | Current sense ratio drift | $I_{OUT} = 1.3\text{ A to } 3.2\text{ A}; I_{OUTCAL} = 2.2\text{ A}; V_{SENSE} = 2\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | -18 | | 18 | % |
| I_{SENSE0} | Analog sense leakage current | $I_{OUT} = 0\text{ A}; V_{SENSE} = 0\text{ V}; V_{IN} = 0\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | 0 | | 1 | μA |
| | | $I_{OUT} = 0\text{ A}; V_{SENSE} = 0\text{ V}; V_{IN} = 5\text{ V}; T_j = -40^\circ\text{C to } 150^\circ\text{C}$ | 0 | | 2 | μA |
| V_{SENSE} | Max analog sense output voltage | $I_{OUT} = 12\text{ A}; R_{SENSE} = 3.9\text{ K}\Omega$ | 5 | | | V |
| V_{SENSEH} | Analog sense output voltage in fault condition ⁽²⁾ | $V_{CC} = 24\text{ V}; R_{SENSE} = 3.9\text{ K}\Omega$ | 7.5 | 8.5 | 9.5 | V |

Table 9. Current sense ($8\text{ V} < V_{CC} < 36\text{ V}$) (continued)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------------|--|--|------|------|------|---------------|
| I_{SENSEH} | Analog sense output current in fault condition ⁽²⁾ | $V_{CC} = 24\text{ V}$; $V_{SENSE} = 5\text{ V}$ | 4.9 | 9 | 12 | mA |
| $t_{DSENSE2H}$ | Delay response time from rising edge of INPUT pin | $V_{SENSE} < 4\text{ V}$; $0.2\text{ A} < I_{OUT} < 12\text{ A}$; $I_{SENSE} = 90\%$ of $I_{SENSE\ max}$; (see Figure 6) | | 200 | 400 | μs |
| $\Delta t_{DSENSE2H}$ | Delay response time between rising edge of output current and rising edge of current sense | $V_{SENSE} < 4\text{ V}$; $I_{SENSE} = 90\%$ of $I_{SENSEMAX}$; $I_{OUT} = 90\%$ of I_{OUTMAX} ; $I_{OUTMAX} = 3\text{ A}$ (see Figure 10) | | | 250 | μs |
| $t_{DSENSE2L}$ | Delay response time from falling edge of INPUT pin | $V_{SENSE} < 4\text{ V}$; $0.2\text{ A} < I_{OUT} < 12\text{ A}$; $I_{SENSE} = 10\%$ of $I_{SENSE\ max}$; (see Figure 6) | | 5 | 20 | μs |

1. Parameter guaranteed by design; it is not tested.
2. Fault condition includes: power limitation, overtemperature and open load in off-state condition.

Table 10. Open-load detection ($V_{FR_stby} = 5\text{ V}$)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|------------------|--|--|------|------|------|---------------|
| V_{OL} | Open-load off-state voltage detection threshold | $V_{IN} = 0\text{ V}$; $8\text{ V} < V_{CC} < 36\text{ V}$ | 2 | | 4 | V |
| t_{DSTKON} | Output short circuit to V_{CC} detection delay at turn off | See Figure 7 | 180 | | 1800 | μs |
| $I_{L(off2)}$ | Off-state output current at $V_{OUT} = 4\text{ V}$ | $V_{IN} = 0\text{ V}$; $V_{SENSE} = 0\text{ V}$; V_{OUT} rising from 0 V to 4 V | -120 | | 0 | μA |
| t_{d_vol} | Delay response from output rising edge to V_{SENSE} rising edge in open-load | $V_{OUT} = 4\text{ V}$; $V_{IN} = 0\text{ V}$; $V_{SENSE} = 90\%$ of V_{SENSEH} ; $R_{SENSE} = 3.9\text{ K}$ | | | 20 | μs |
| t_{DFRSTK_ON} | Output short circuit to V_{CC} detection delay at FRSTBY activation | See Figure 9 ; Input _{1,2} = low | | | 50 | μs |

Figure 6. Current sense delay characteristics

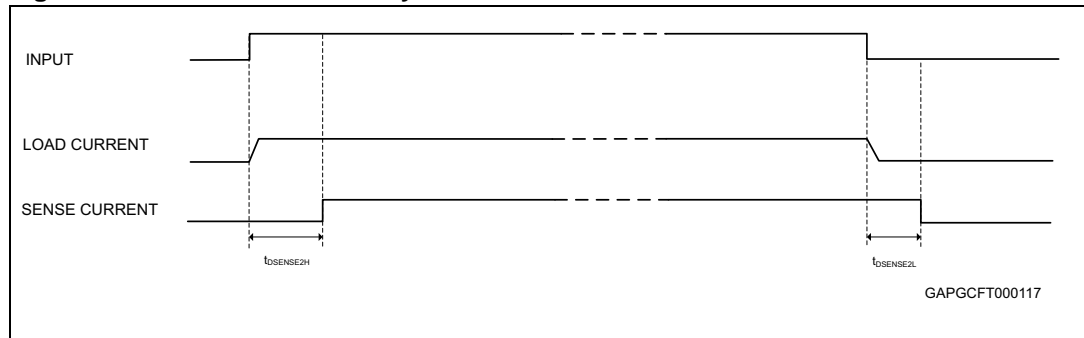
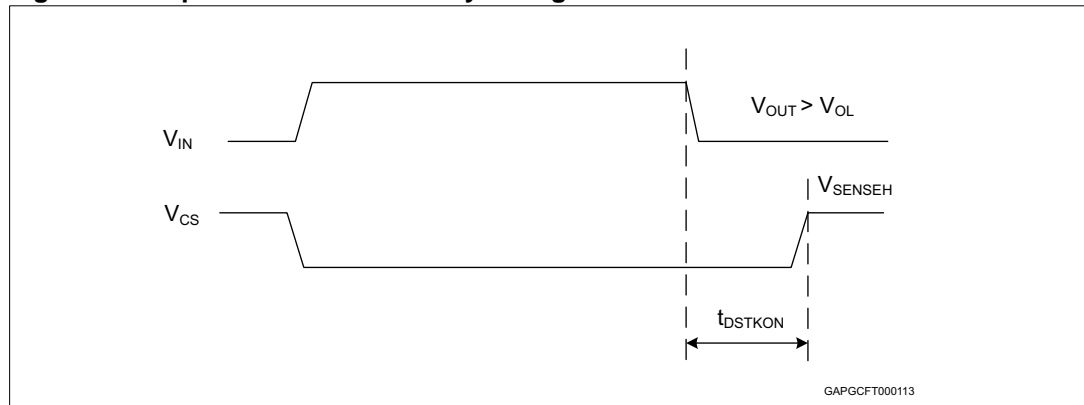


Figure 7. Open-load off-state delay timing



Note: $V_{fr_stby} = high$

Figure 8. Switching characteristics

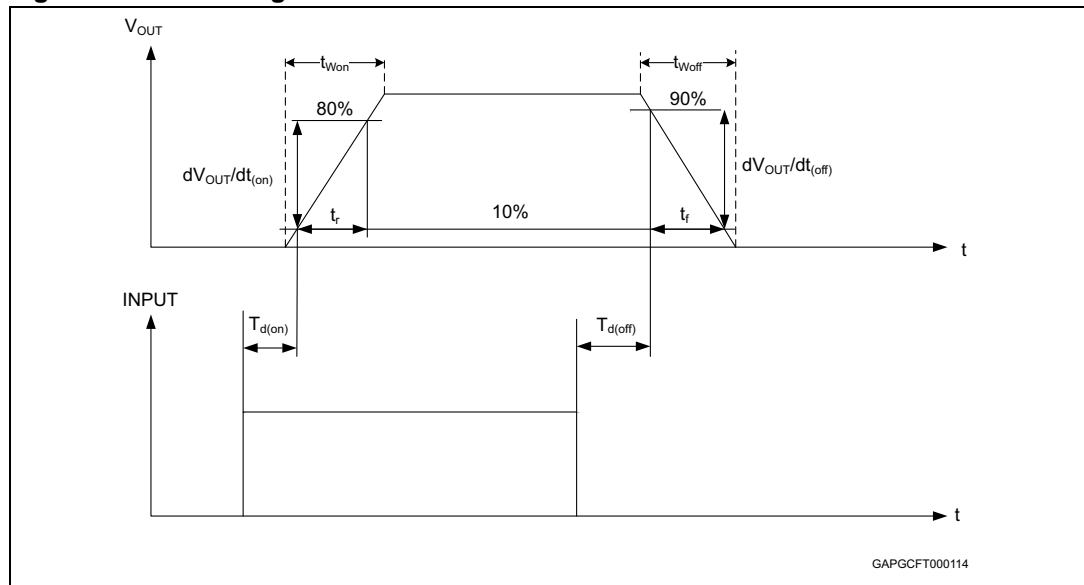


Figure 9. Output stuck to V_{CC} detection delay time at FR_{STBY} activation

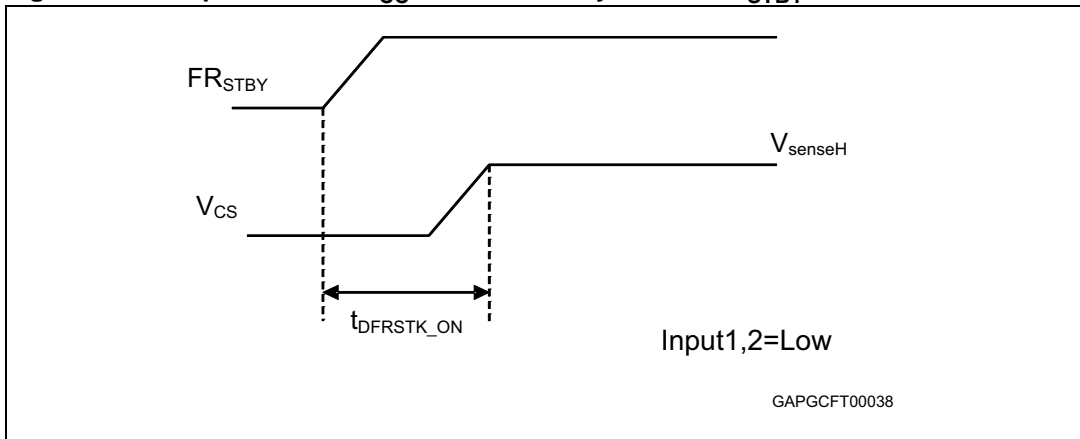


Figure 10. Delay response time between rising edge of output current and rising edge of current sense

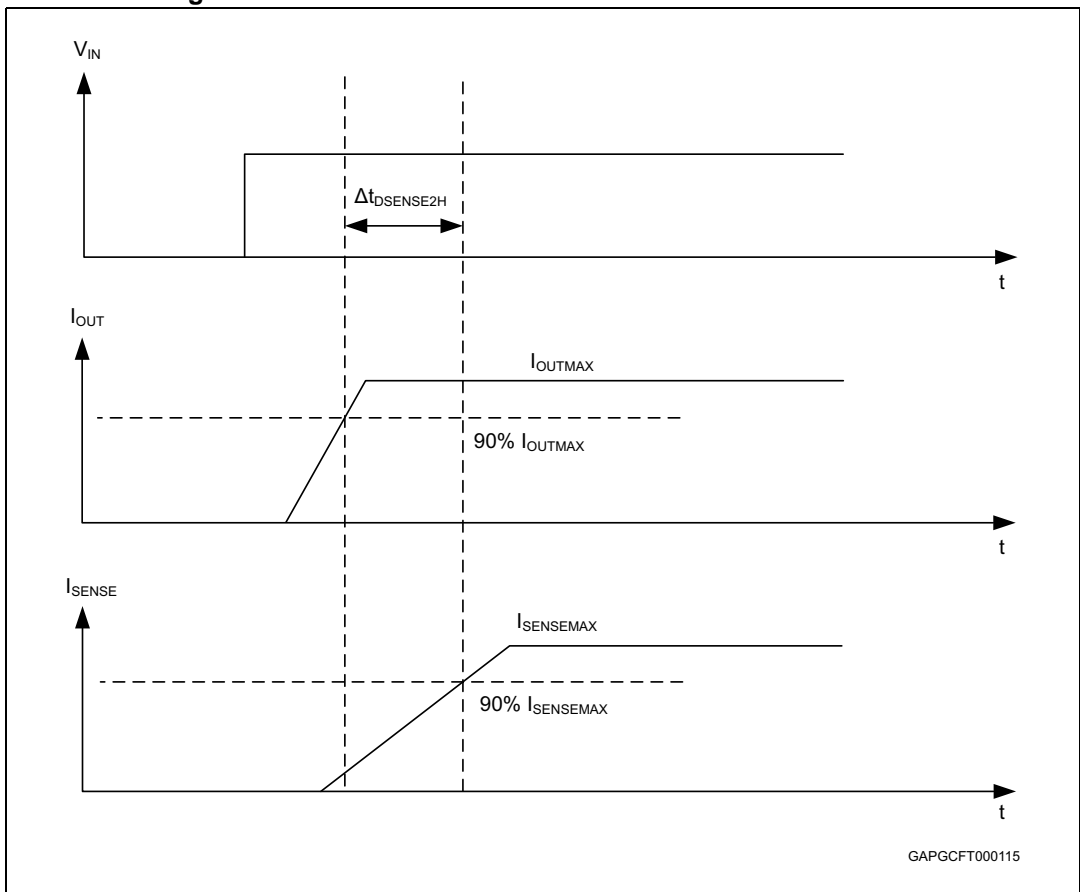


Figure 11. Output voltage drop limitation

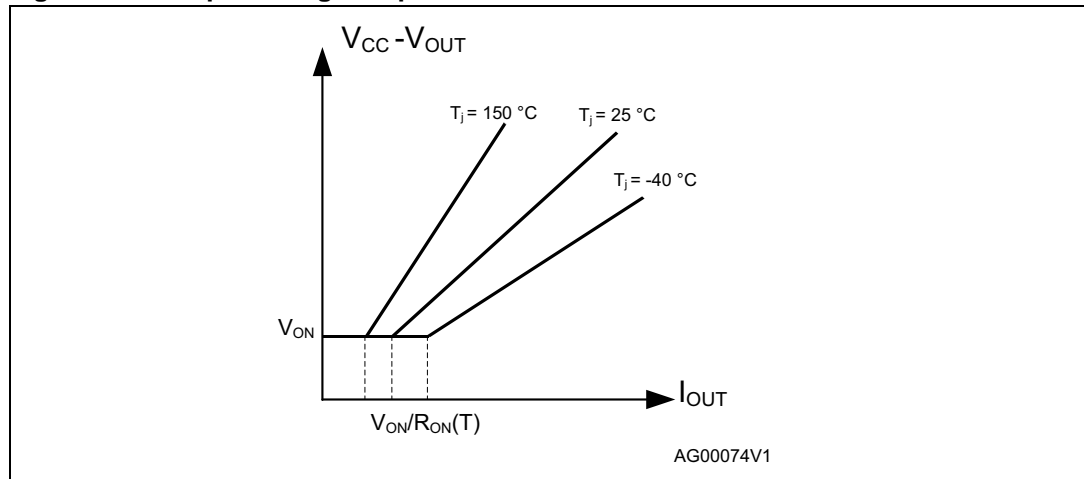


Figure 12. Device behavior in overload condition

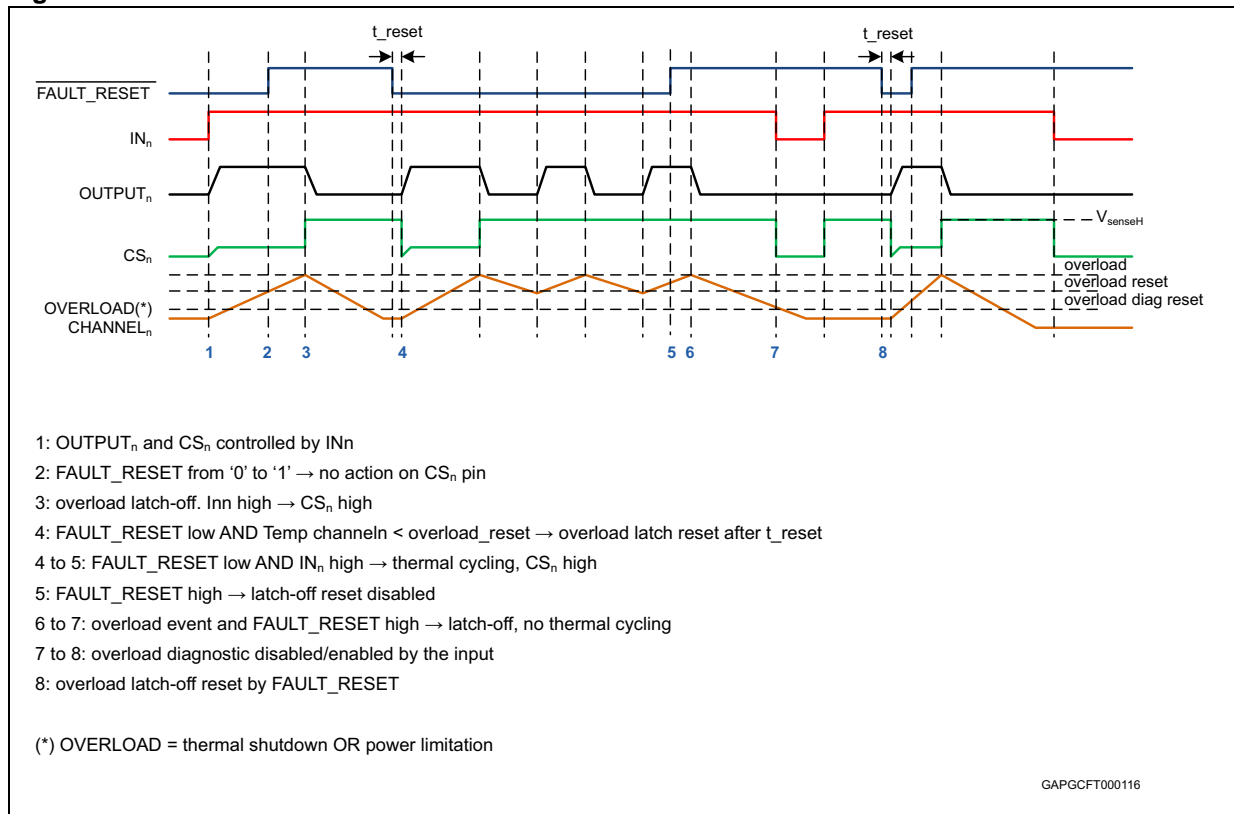


Table 11. Truth table

| Conditions | Fault reset standby | Input | Output | Sense |
|------------------------------------|---------------------|-------|----------|--------------|
| Standby | L | L | L | 0 |
| Normal operation | X | L | L | 0 |
| | X | H | H | Nominal |
| Overload | X | L | L | 0 |
| | X | H | H | > Nominal |
| Overtemperature / short to ground | X | L | L | 0 |
| | L | H | Cycling | V_{SENSEH} |
| | H | H | Latched | V_{SENSEH} |
| Undervoltage | X | X | L | 0 |
| Short to V_{BAT} | L | L | H | 0 |
| | H | L | H | V_{SENSEH} |
| | X | H | H | < Nominal |
| Open load off-state (with pull-up) | L | L | H | 0 |
| | H | L | H | V_{SENSEH} |
| | X | H | H | 0 |
| Negative output voltage clamp | X | L | Negative | 0 |

Table 12. Electrical transient requirements (part 1)

| ISO 7637-2: 2004(E) Test pulse | Test levels ⁽¹⁾ | | Number of pulses or test times | Burst cycle/pulse repetition time | | Delays and impedance |
|--------------------------------------|----------------------------|---------|--------------------------------------|--------------------------------------|--------|-------------------------|
| | III | IV | | | | |
| 1 | - 450 V | - 600 V | 5000 pulses | 0.5 s | 5 s | 1 ms, 50 Ω |
| 2a | + 37 V | + 50 V | 5000 pulses | 0.2 s | 5 s | 50 μs, 2 Ω |
| 3a | - 150 V | - 200 V | 1h | 90 ms | 100 ms | 0.1 μs, 50 Ω |
| 3b | + 150 V | + 200 V | 1h | 90 ms | 100 ms | 0.1 μs, 50 Ω |
| 4 | - 12 V | - 16 V | 1 pulse | | | 100 ms, 0.01 Ω |
| 5b ⁽¹⁾ | + 123 V | + 174 V | 1 pulse | | | 350 ms, 1 Ω |

1. Valid in case of external load dump clamp: 58 V maximum referred to ground.

Table 13. Electrical transient requirements (part 2)⁽¹⁾

| ISO 7637-2: 2004(E) Test pulse | Test level results | |
|--------------------------------------|--------------------|----|
| | III | IV |
| 1 | C | C |
| 2a | C | C |
| 3a | C | C |
| 3b ⁽²⁾ | E | E |
| 3b ⁽³⁾ | C | C |
| 4 | C | C |
| 5b ⁽⁴⁾ | C | C |

1. In order to guarantee the ISO transient classes a minimum 10KΩ protection resistors are needed on logic pins
2. Without capacitor between V_{CC} and GND.
3. With 10 nF between V_{CC} and GND.
4. External load dump clamp, 58 V maximum, referred to ground.

Table 14. Electrical transient requirements (part 3)

| Class | Contents |
|-------|--|
| C | All functions of the device are performed as designed after exposure to disturbance. |
| E | One or more functions of the device are not performed as designed after exposure to disturbance and cannot be returned to proper operation without replacing the device. |

2.4 Electrical characteristics curves

Figure 13. Off-state output current

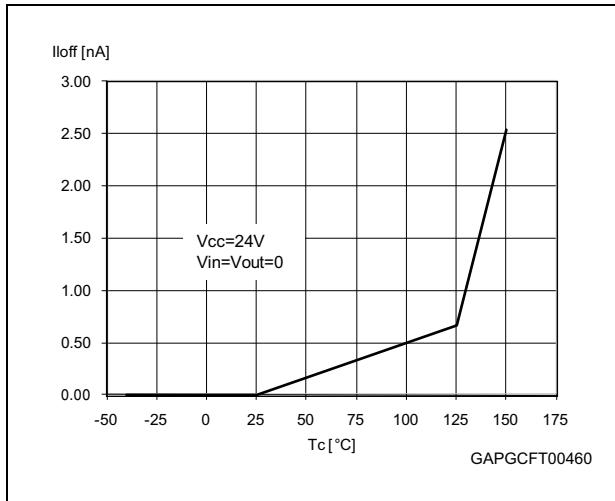


Figure 14. High-level input current

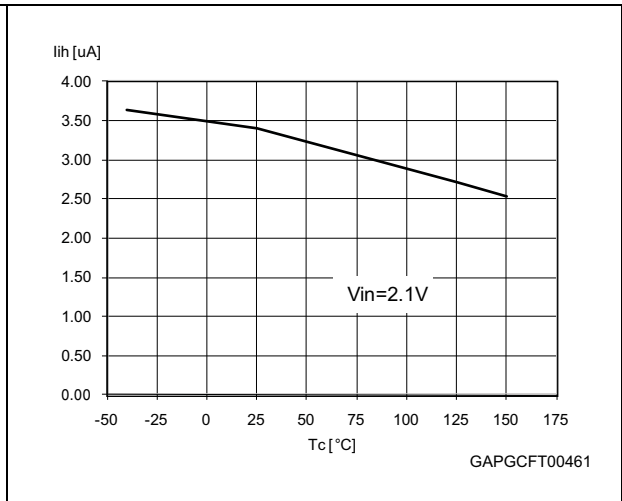


Figure 15. Input clamp voltage

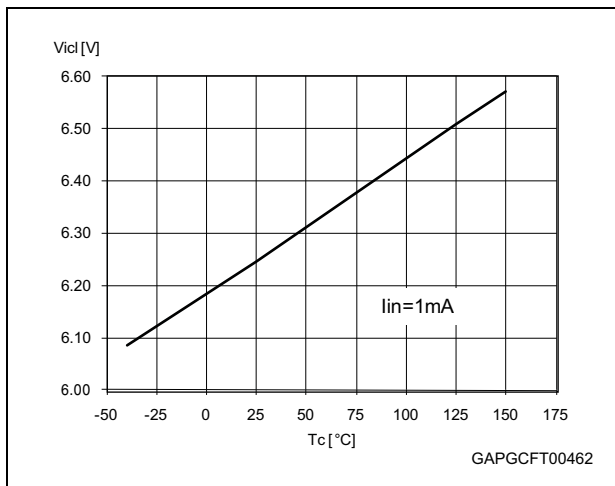


Figure 16. High-level input voltage

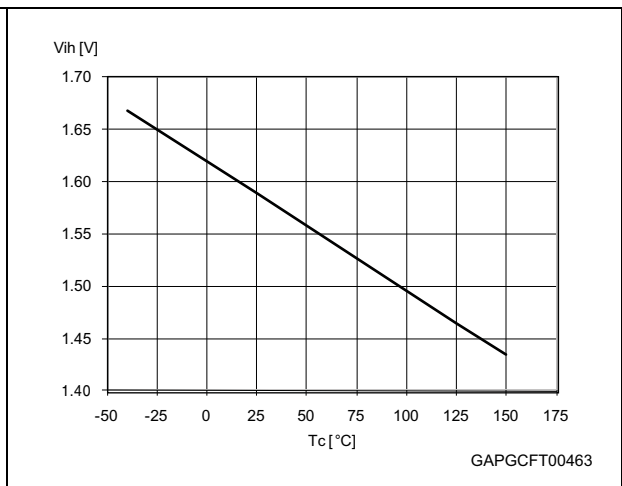


Figure 17. Low-level input voltage

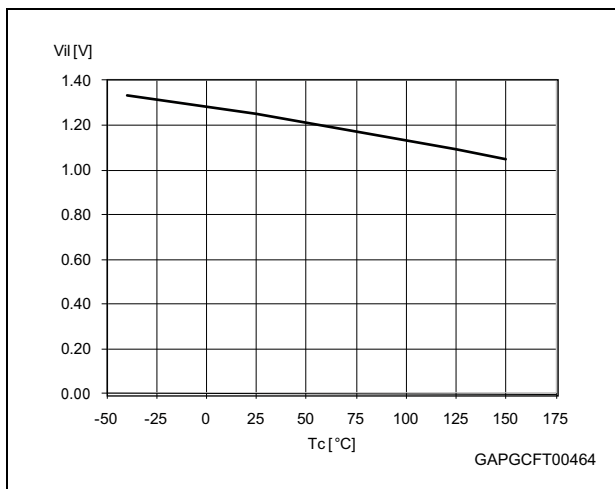


Figure 18. Input hysteresis voltage

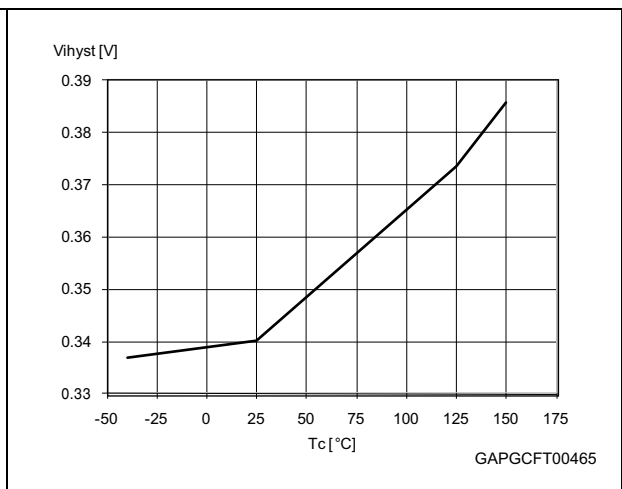


Figure 19. On-state resistance vs T_{case}

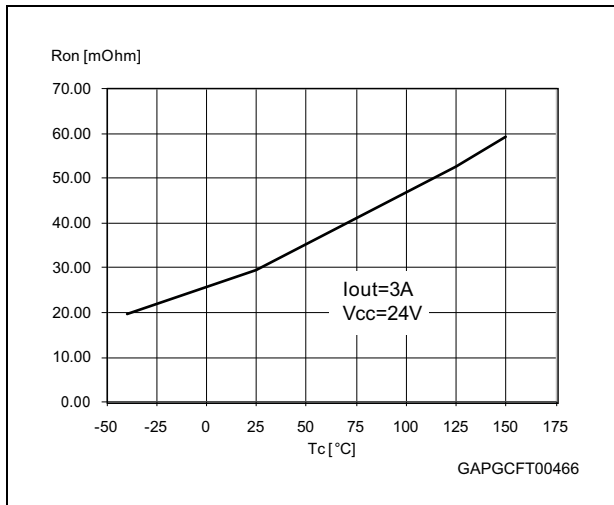


Figure 20. On-state resistance vs V_{CC}

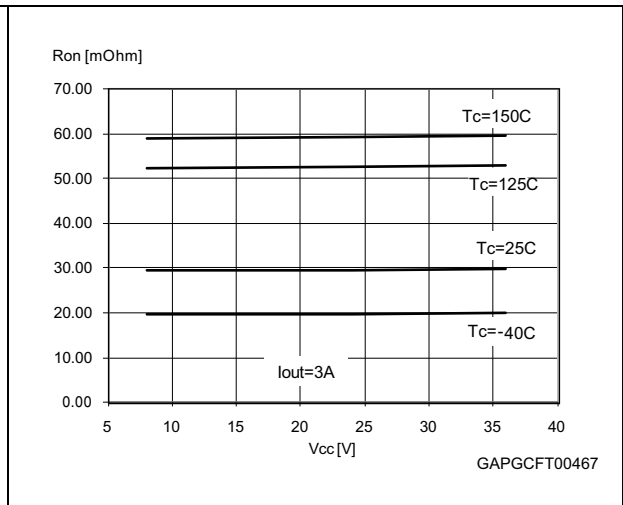


Figure 21. I_{LIMH} vs T_{case}

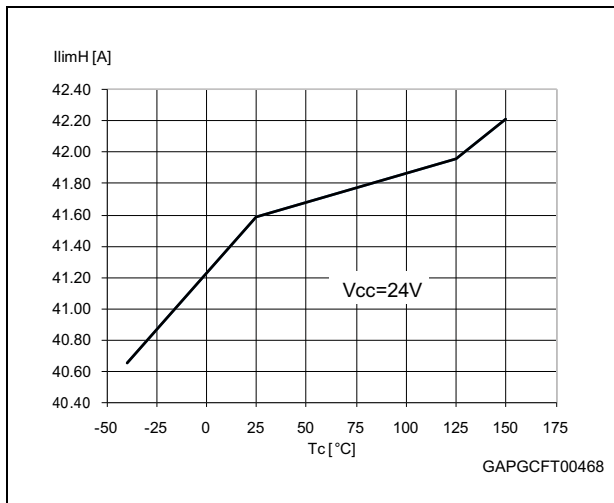


Figure 22. Turn-on voltage slope

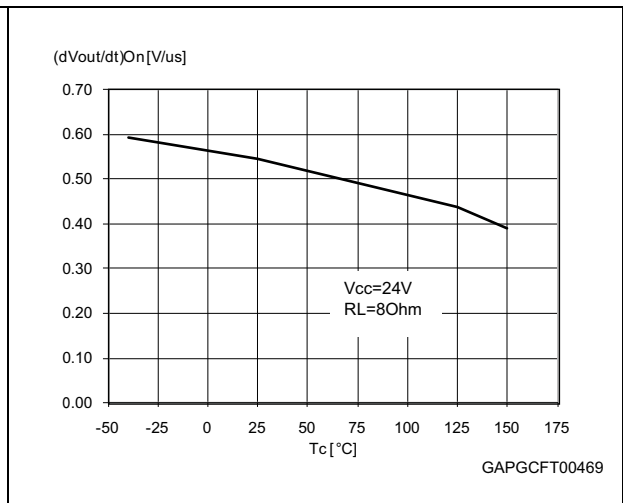
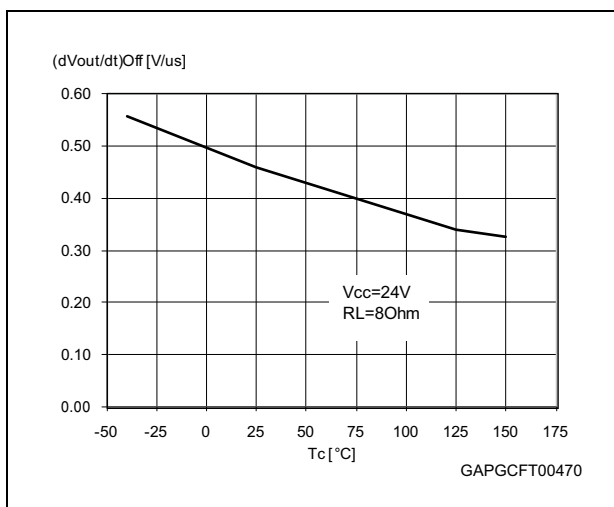


Figure 23. Turn-off voltage slope



3.1.2 Solution 2: diode (D_{GND}) in the ground line

A resistor ($R_{GND} = 4.7 \text{ k}\Omega$) should be inserted in parallel to D_{GND} if the device drives an inductive load.

This small signal diode can be safely shared amongst several different HSDs. Also in this case, the presence of the ground network produces a shift ($\approx 600 \text{ mV}$) in the input threshold and in the status output values, if the microprocessor ground is not common to the device ground. This shift does not vary if more than one HSD shares the same diode/resistor network.

3.2 Load dump protection

D_{ld} is necessary (Voltage Transient Suppressor) if the load dump peak voltage exceeds to V_{CC} maximum DC rating. The same applies if the device is subject to transients on the V_{CC} line that are greater than the ones shown in the ISO T/R 7637/2 table.

3.3 MCU I/Os protection

If a ground protection network is used and negative transient is present on the V_{CC} line, the control pins are pulled negative. ST suggests that a resistor (R_{prot}) have to be inserted in line to prevent the microcontroller I/O pins from latching-up.

The value of these resistors is a compromise between the leakage current of the microcontroller and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of microcontroller I/Os.

$$-V_{CCpeak}/I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

Calculation example:

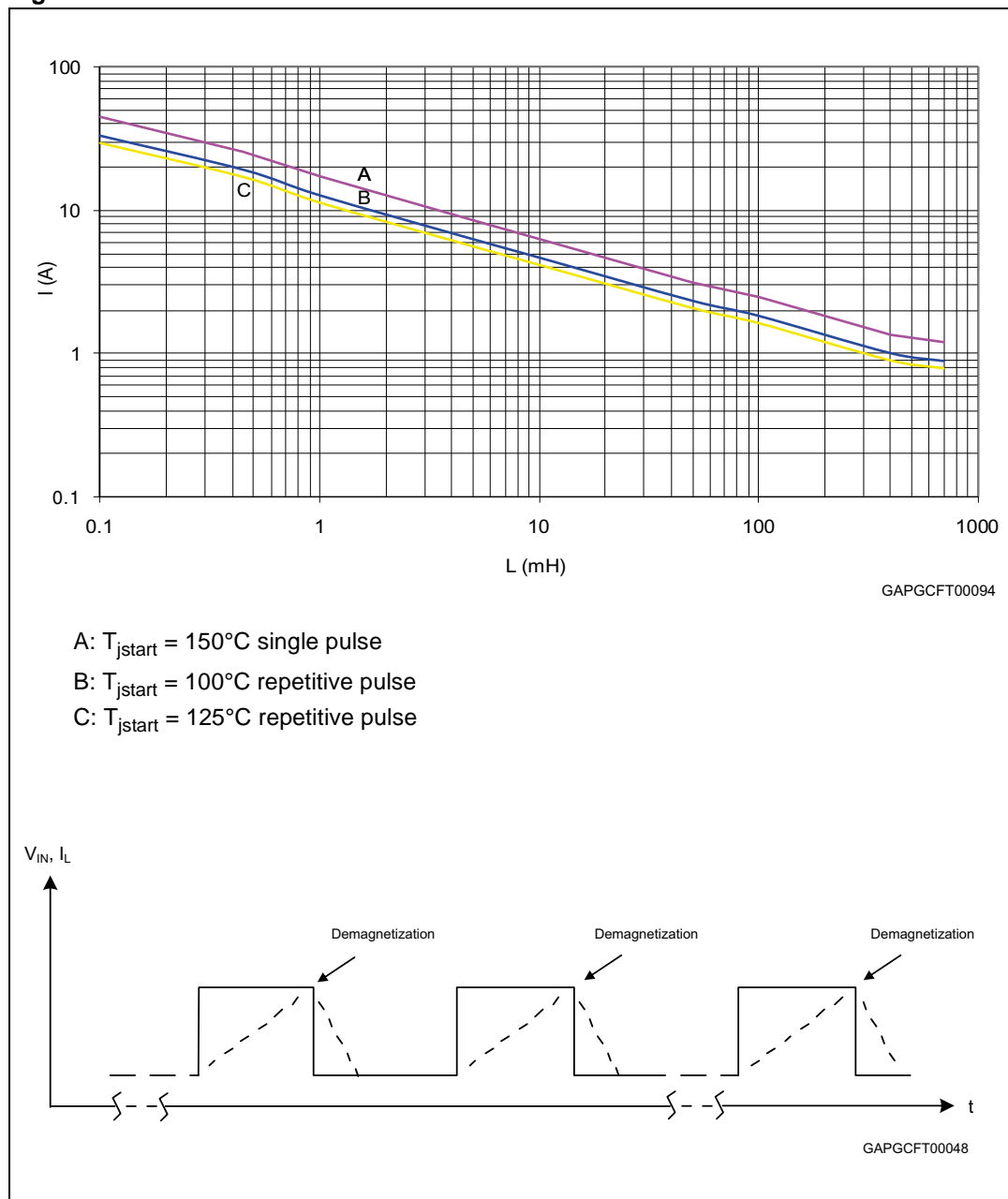
For $V_{CCpeak} = -600 \text{ V}$ and $I_{latchup} \geq 20 \text{ mA}$; $V_{OH\mu C} \geq 4.5 \text{ V}$

$$30 \text{ k}\Omega \leq R_{prot} \leq 180 \text{ k}\Omega.$$

Recommended R_{prot} value is $60 \text{ k}\Omega$.

3.4 Maximum demagnetization energy ($V_{CC} = 24\text{ V}$)

Figure 25. Maximum turn-off current versus inductance

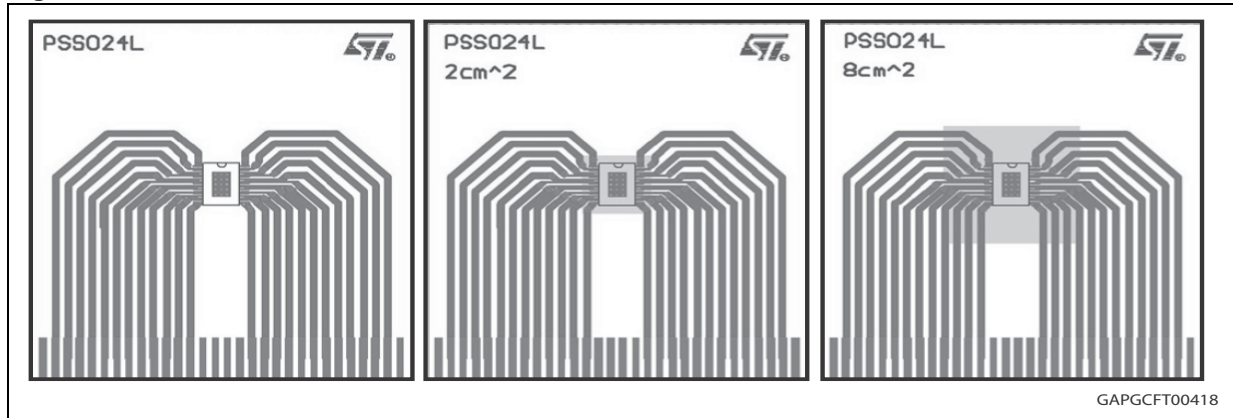


Note: Values are generated with $R_L = 0\ \Omega$. In case of repetitive pulses, T_{jstart} (at the beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves A and B.

4 Package and PCB thermal data

4.1 PowerSSO-24 thermal data

Figure 26. PowerSSO-24 PC board



1. Layout condition of R_{th} and Z_{th} measurements (PCB: double layer, thermal vias, FR4 area = 77 mm x 86 mm, PCB thickness = 1.6 mm, Cu thickness = 70 μ m (front and back side), Copper areas: from minimum pad lay-out to 8 cm²).

Figure 27. $R_{thj-amb}$ vs PCB copper area in open box free air condition (one channel ON)

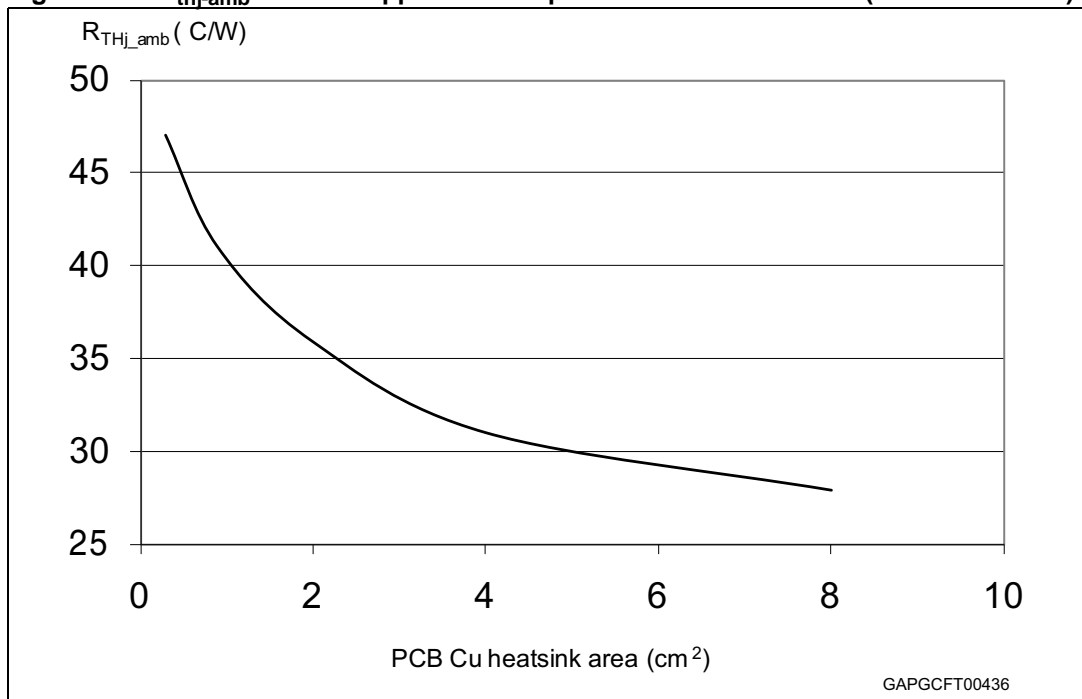


Figure 28. PowerSSO-24 thermal impedance junction ambient single pulse (one channel ON)

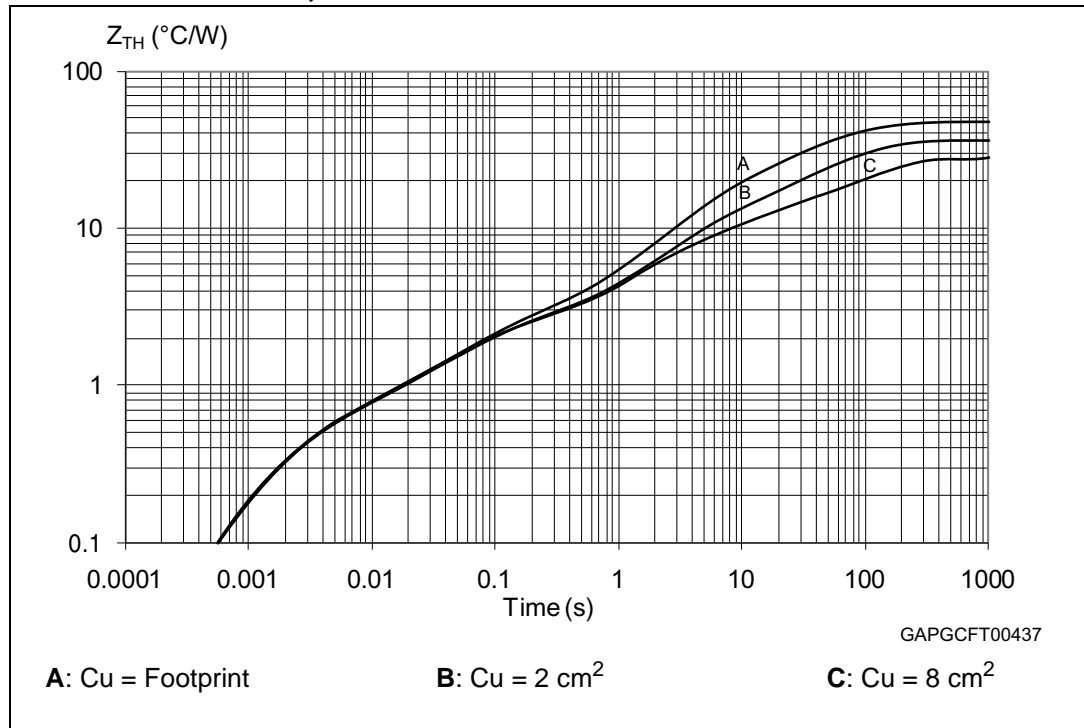
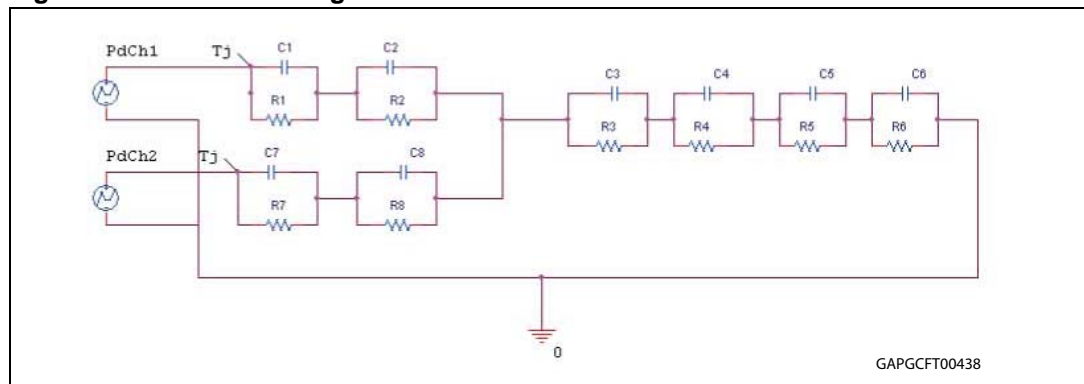


Figure 29. Thermal fitting model of a double channel HSD in PowerSSO-24⁽¹⁾



1. The fitting model is a simplified thermal tool and is valid for transient evolutions where the embedded protections (power limitation or thermal cycling during thermal shutdown) are not triggered

Equation 1: Pulse calculation formula

$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1 - \delta)$$

where $\delta = t_p/T$

Table 15. Thermal parameters

| Area/island (cm ²) | Footprint | 2 | 8 |
|--------------------------------|-----------|----|----|
| R1 (°C/W) | 0,5 | — | — |
| R2 (°C/W) | 0.75 | — | — |
| R3 (°C/W) | 1 | — | — |
| R4 (°C/W) | 7.7 | — | — |
| R5 (°C/W) | 9 | 9 | 8 |
| R6 (°C/W) | 28 | 17 | 10 |
| R7 (°C/W) | 0,5 | — | — |
| R8 (°C/W) | 0.75 | — | — |
| C1 (W.s/°C) | 0,005 | — | — |
| C2 (W.s/°C) | 0,05 | — | — |
| C3 (W.s/°C) | 0,1 | — | — |
| C4 (W.s/°C) | 0,5 | — | — |
| C5 (W.s/°C) | 1 | 4 | 9 |
| C6 (W.s/°C) | 2.2 | 5 | 17 |
| C7 (W.s/°C) | 0,005 | — | — |
| C8 (W.s/°C) | 0,05 | — | — |

5 Package and packing information

5.1 ECOPACK®

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

5.2 PowerSSO-24 package information

Figure 30. PowerSSO-24 package dimensions

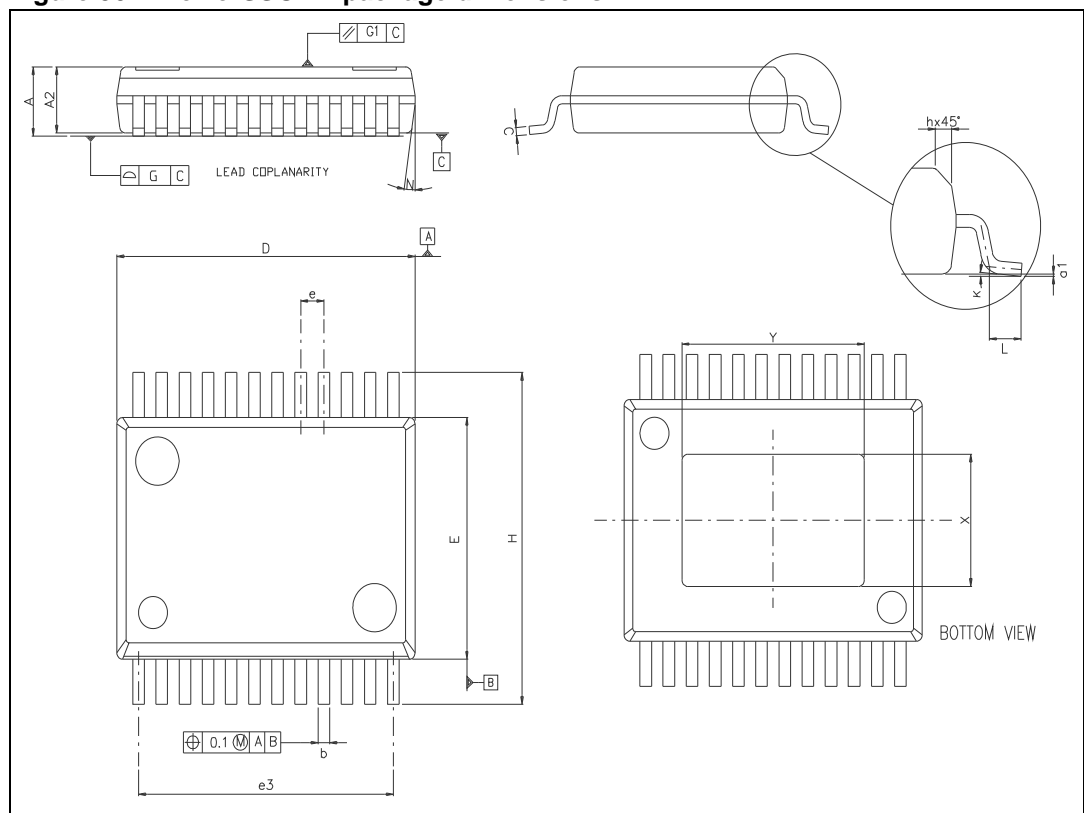


Table 16. PowerSSO-24 mechanical data

| Symbol | Millimeters | | |
|--------|-------------|------|-------|
| | Min. | Typ. | Max. |
| A | 2.15 | | 2.47 |
| A2 | 2.15 | | 2.40 |
| a1 | 0 | | 0.075 |
| b | 0.33 | | 0.51 |
| c | 0.23 | | 0.32 |
| D | 10.10 | | 10.50 |
| E | 7.4 | | 7.6 |
| e | | 0.8 | |
| e3 | | 8.8 | |
| G | | | 0.1 |
| G1 | | | 0.06 |
| H | 10.1 | | 10.5 |
| h | | | 0.4 |
| k | | 5° | |
| L | 0.55 | | 0.85 |
| N | | | 10° |
| X | 4.1 | | 4.7 |
| Y | 6.5 | | 7.1 |

5.3 PowerSSO-24 packing information

Figure 31. PowerSSO-24 tube shipment (no suffix)

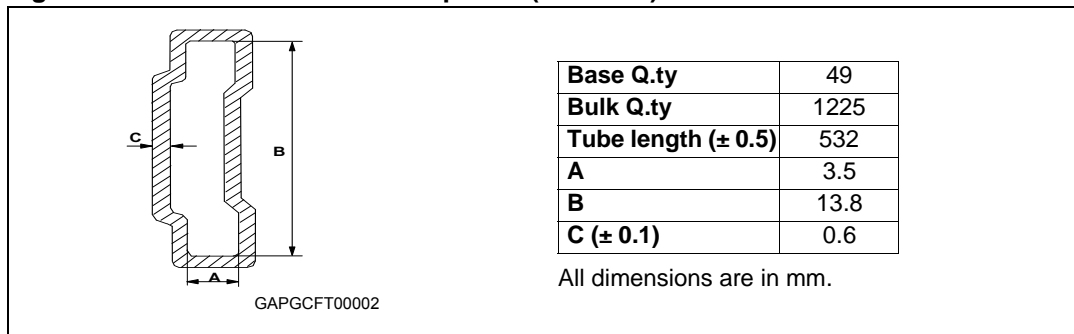
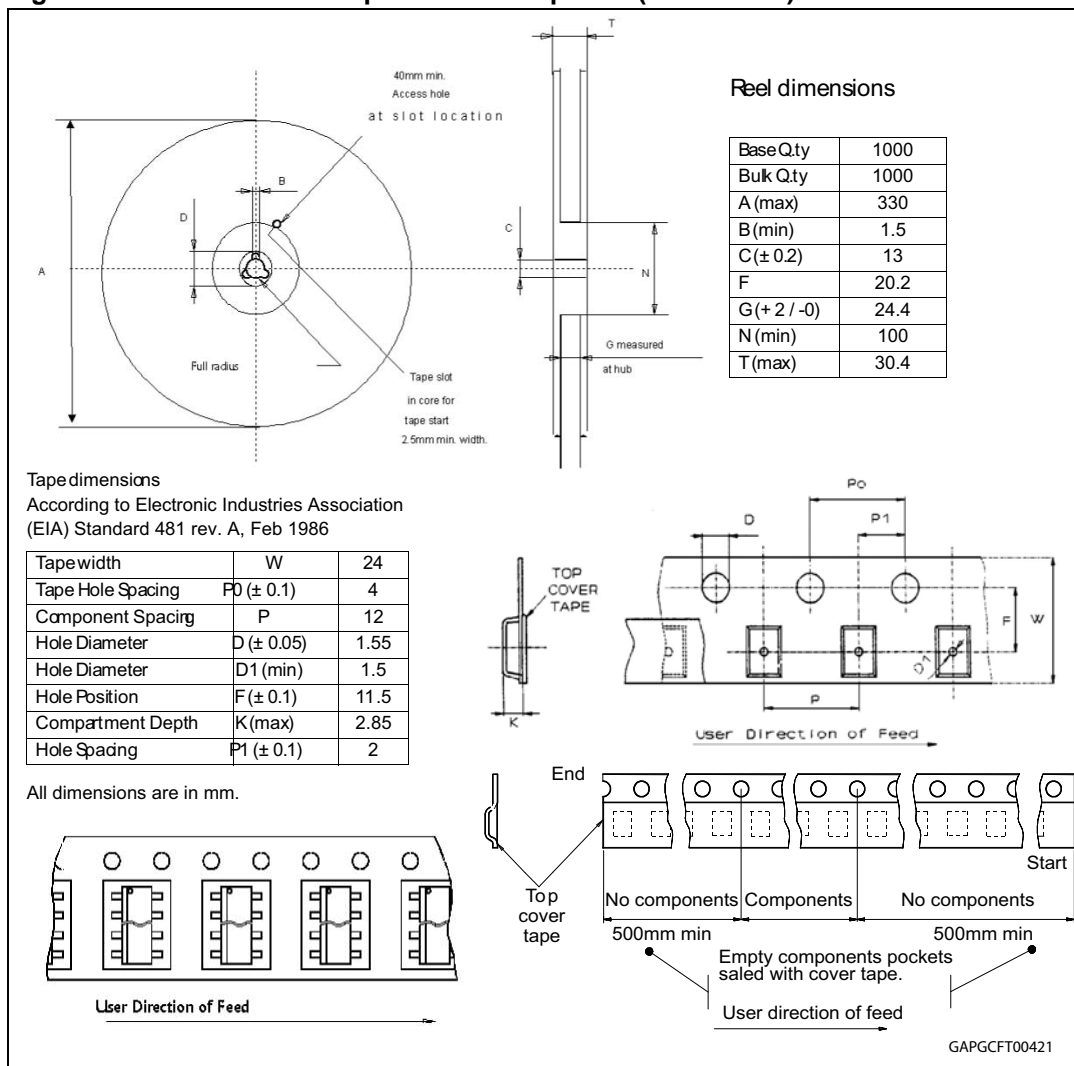


Figure 32. PowerSSO-24 tape and reel shipment (suffix “TR”)



6 Order codes

Table 17. Device summary

| Package | Order codes | |
|-------------|---------------|-----------------|
| | Tube | Tape and reel |
| PowerSSO-24 | VND5T035LAK-E | VND5T035LAKTR-E |

7 Revision history

Table 18. Document revision history

| Date | Revision | Changes |
|-------------|-----------------|---|
| 15-Jun-2012 | 1 | Initial release. |
| 19-Jun-2012 | 2 | Changed document state form "Target specification" to "Production data" |
| 18-Sep-2013 | 3 | Updated disclaimer. |

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